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could hereinbefore.

Please replace paragraph [0185] as follows:

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[0185] When the substrate surfaces are cleaned with a hydrogen fluoride (HF) solution or the like after the selective or preferential growth of the tungsten films 26c, 35c, a tungsten film is grown on the silicon oxide film (i.e. breakage of the selectivity occurs) as shown in Fig. 27a. If a tungsten film is grown on a contaminant metal on the silicon oxide film as described with reference to Embodiment 5, the unnecessary tungsten film and contaminant metal are etched, thereby providing a highly reliable tungsten film.

IN THE CLAIMS:

Please **amend**, furthermore, claims 3, 6, 7, 15, 41, 51 and 52, as follows:

3. (Twice Amended) A method for manufacturing a semiconductor integrated circuit device, comprising the steps of:

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- (a) forming a first wiring on a semiconductor substrate;
 - (b) forming a first insulating film on said first wiring;
 - (c) removing said first insulating film at a portion thereof corresponding to a contact region of said first wiring to form a contact hole;
 - (d) forming a first conductive film over said first insulating film including the inside of said contact hole;
 - (e) removing said first conductive film from outside of said contact hole to form a plug;
 - (f) forming a second insulating film over said first insulating film and said plug;

(g) removing said second insulating film at a portion thereof corresponding to a region where a second wiring is to be formed, thereby forming a groove for wiring;

(h) successively forming a barrier layer and a second conductive film on said second insulating film including the inside of the said groove for wiring;

(i) removing said barrier layer and said second conductive film from outside of said groove for wiring by polishing to form a second wiring;

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(j) cleaning a surface of said second insulating film to remove said second conductive film that remains on said second insulating film in said step (i);

(k) forming a cap conductive film on said second wiring in self-alignment with said second wiring by selective growth or preferential growth of said cap conductive film on said second wiring; and

(l) forming a third insulating film over said cap conductive film and said second insulating film.

6. (Twice Amended) A method for manufacturing a semiconductor integrated circuit device according to Claim 4 or 5 further comprising the steps of:

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partly removing said third insulating film to form an opening so that said cap conductive film is exposed;

burying a conductive material in said opening to form a plug; and

forming an upper wiring, which extends on said plug, on said third insulating film.

7. (Twice Amended) A method for manufacturing a semiconductor integrated circuit device according to Claim 3, 4 or 5, wherein said second wiring is made of copper, silver, aluminum or an alloy containing these metals as a main component.

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15. (Twice Amended) A method for manufacturing a semiconductor integrated circuit device according to Claim 1, wherein said cleaning in said step (c) is performed by using a solution containing at least one of hydrogen fluoride (HF), citric acid, oxalic acid, hydrogen peroxide (H₂O₂), hydrochloric acid (HCl), sulfuric acid (H₄SO₄), ammonia (NH₃) and aminoethanol.

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41. (Twice Amended) A method for manufacturing a semiconductor integrated circuit device according to Claim 39, wherein said cleaning in said step (d) is a cleaning with a solution containing at least one of hydrogen fluoride (HF), citric acid, oxalic acid, hydrogen peroxide (H₂O₂), hydrochloric acid (HCl), sulfuric acid, ammonia (NH₃) and aminoethanol.

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51. (Amended) A method for manufacturing semiconductor integrated circuit device according to claim 4, said cleaning in said step (g) is performed by using a solution containing at least one of hydrogen fluoride (HF), citric acid, oxalic acid, hydrogen peroxide (H₂O₂), hydrochloric acid (HCl), sulfuric acid (H₄SO₄), ammonia (NH₃) and aminoethanol.

52. (Amended) A method for manufacturing semiconductor integrated circuit device according to claim 5, said cleaning in said step (g) is performed by using a solution containing at least one of hydrogen fluoride (HF), citric acid, oxalic acid, hydrogen peroxide (H₂O₂), hydrochloric acid (HCl), sulfuric acid (H₄SO₄), ammonia (NH₃) and aminoethanol.

Please insert new claims 55 – 57, as follows:

55. A method for manufacturing a semiconductor integrated circuit device according to claim 1, further comprising the steps of:

(a) partly removing said second insulating film to form an opening so that said cap conductive film is exposed;

(b) burying a conductive material in said opening to form a plug; and

(c) forming an upper wiring, which extends on said plug, on said second insulating film.

56. A method for manufacturing a semiconductor integrated circuit device according to claim 1, wherein said wiring is made of copper, silver, aluminum or an alloy containing these metals as a main component.

57. A method for manufacturing a semiconductor integrated circuit device according to claim 2, wherein said wiring is made of copper, silver, aluminum or an alloy containing these metals as a main component.
